

SDB310Q

Schottky Barrier Diode

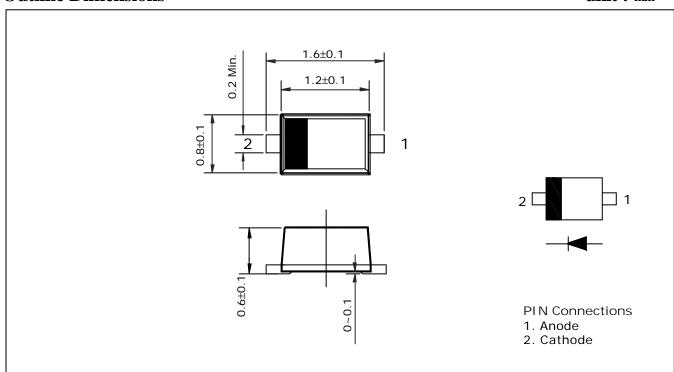
Features

- · Low power rectified
- Silicon epitaxial type
- High reliability

Ordering Information

| Type No. | Marking Package Cod | | |
|----------|---------------------|---------|--|
| SDB310Q | S2 | SOD-523 | |

Outline Dimensions unit: mm



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Absolute maximum ratings

Ta=25°C

| Characteristic | Symbol | Ratings | Unit |
|---|--------------------|-----------|------|
| Reverse voltage | V_R | 30 | V |
| Repetitive peak forward current | I _{FRM} * | 0.5 | А |
| Forward current | I _F | 0.2 | А |
| Non-repetitive peak forward current(10ms) | I _{FSM} | 2 | А |
| Power dissipation | P _D | 150 | mW |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | T _{stg} | -55 ~ 150 | °C |

^{* :} $\delta = D/T = 0.33$ (T<1S)



^{* :} Unit ratings. Total rating=Unit rating×1.5

Electrical Characteristics

Ta=25° C

| Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|-----------------------|-----------------|---|------|------|------|------|
| Forward voltage 1 | $V_{F(1)}$ | $I_F = 10 \text{mA}$ | - | - | 0.4 | V |
| Forward voltage 2 | $V_{F(2)}$ | I _F =30mA | - | - | 0.5 | V |
| Reverse current | I _R | $V_R = 30V$ | - | - | 1 | μΑ |
| Total capacitance | Ст | V _R =1V, f=1MHz | - | - | 10 | pF |
| Reverse recovery time | t _{rr} | $I_F = I_R = 10$ mA, $I_{RR} = 1$ mA, $R_L = 100\Omega$ | - | - | 5 | ns |

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Electrical Characteristic Curves

Fig. 1 I_F - V_F

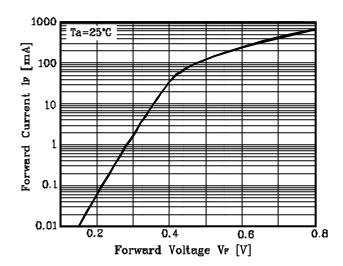


Fig. 2 I_R - V_R

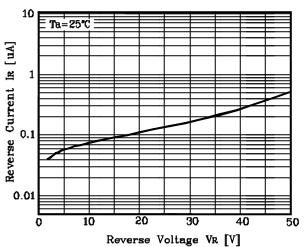
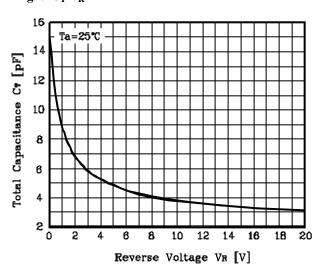


Fig. 3 C_T - V_R



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